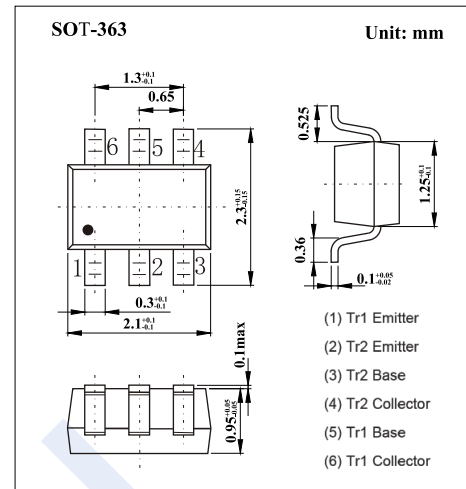
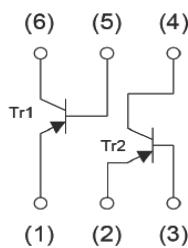


## PNP Transistors

## UMT2N

## ■ Features

- Collector Current Capability  $I_C = -150\text{mA}$
- Collector Emitter Voltage  $V_{CE0} = -50\text{V}$

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-60	V
Collector - Emitter Voltage	$V_{CE0}$	-50	
Emitter - Base Voltage	$V_{EB0}$	-6	
Collector Current - Continuous	$I_C$	-150	mA
Collector Power Dissipation	$P_C$	150	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = -100\ \mu\text{A}$ , $I_E = 0$	-60			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = -1\ \text{mA}$ , $I_B = 0$	-50			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100\ \mu\text{A}$ , $I_C = 0$	-6			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -60\ \text{V}$ , $I_E = 0$			-100	nA
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -6\ \text{V}$ , $I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\ \text{mA}$ , $I_B = -5\ \text{mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\ \text{mA}$ , $I_B = -5\ \text{mA}$			-1.2	
DC current gain	$h_{FE}$	$V_{CE} = -6\ \text{V}$ , $I_C = -1\ \text{mA}$	120		560	
Collector output capacitance	$C_{ob}$	$V_{CB} = -12\ \text{V}$ , $I_E = 0$ , $f = 1\ \text{MHz}$			5	pF
Transition frequency	$f_T$	$V_{CE} = -12\ \text{V}$ , $I_C = -2\ \text{mA}$ , $f = 100\ \text{MHz}$		140		MHz

## ■ Marking

Marking	T2
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## PNP Transistors

## UMT2N

- Typical Characteristics  
<For Tr1 and Tr2 in common>

Fig.1 Ground Emitter Propagation Characteristics

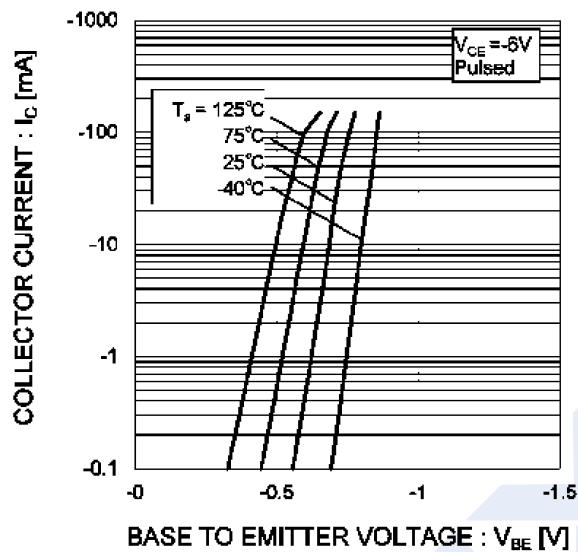


Fig.2 Grounded Emitter Output Characteristics

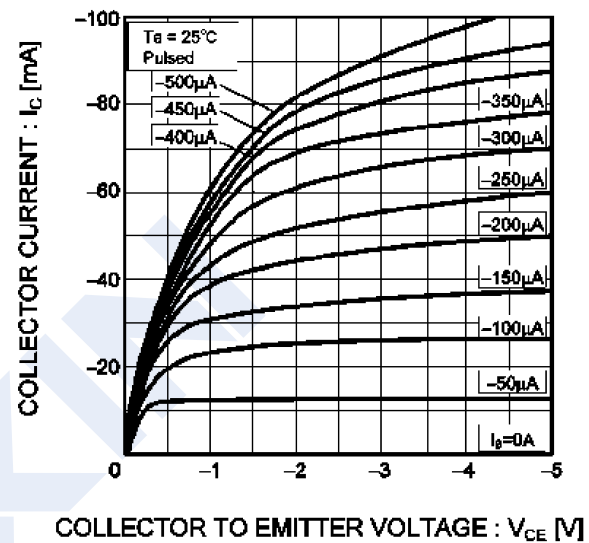


Fig.3 DC Current Gain vs. Collector Current (I)

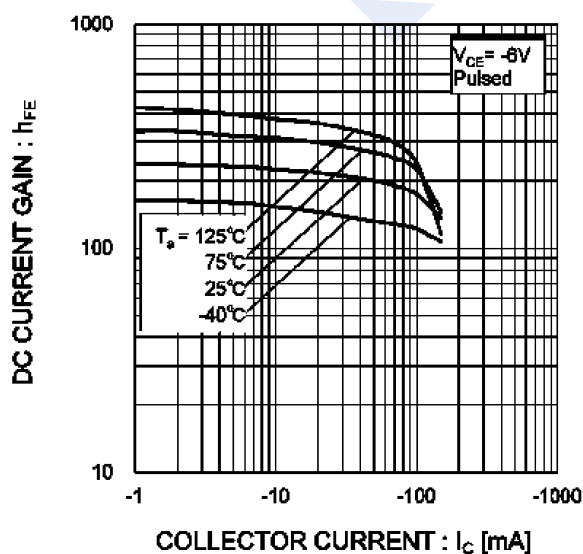
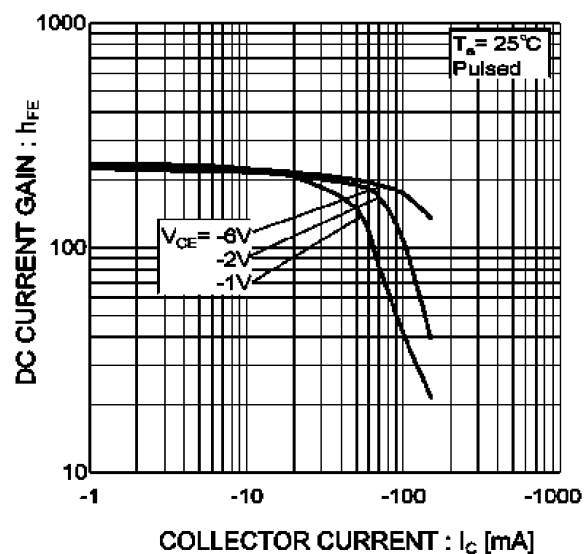


Fig.4 DC Current Gain vs. Collector Current (II)



# PNP Transistors

## UMT2N

■ Typical Characteristics

<For Tr1 and Tr2 in common>

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current(I)

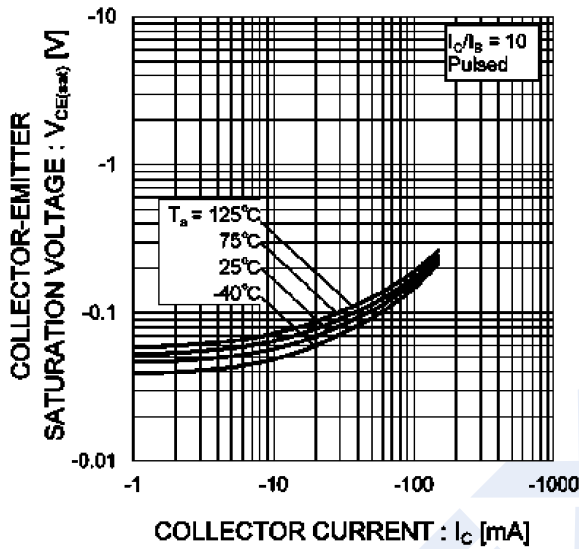


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current(II)

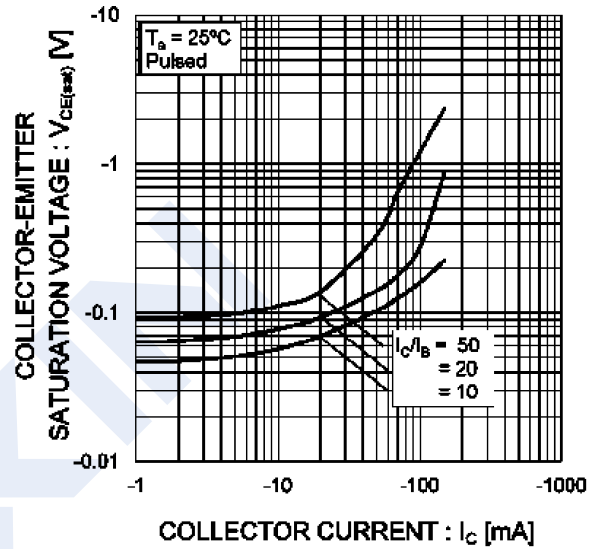


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current (I)

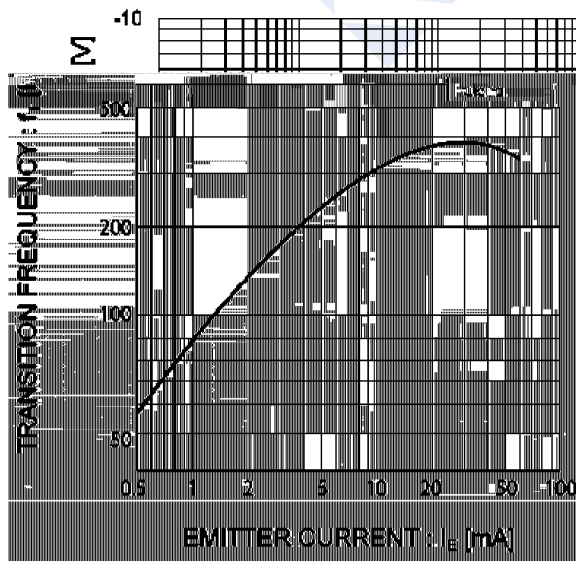
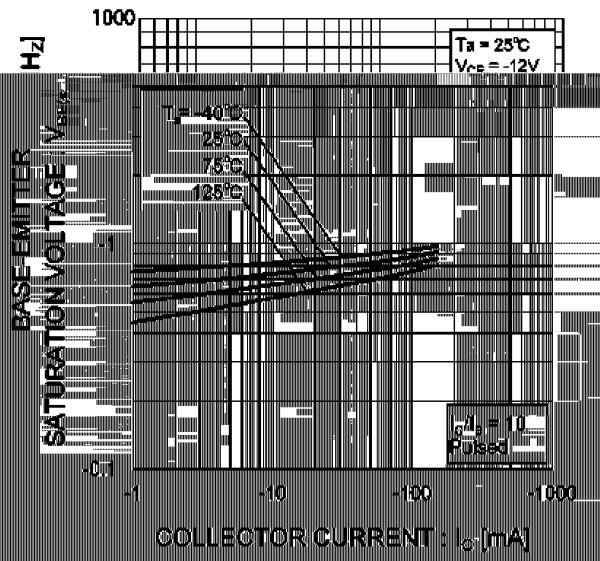


Fig.8 Gain Bandwidth Product vs. Emitter Current



## PNP Transistors

## UMT2N

## ■ Typical Characteristics

<For Tr1 and Tr2 in common>

Fig.9 Collector Output Capacitance vs.  
Collector-Base Voltage  
Emitter Input Capacitance vs.  
Emitter-Base Voltage

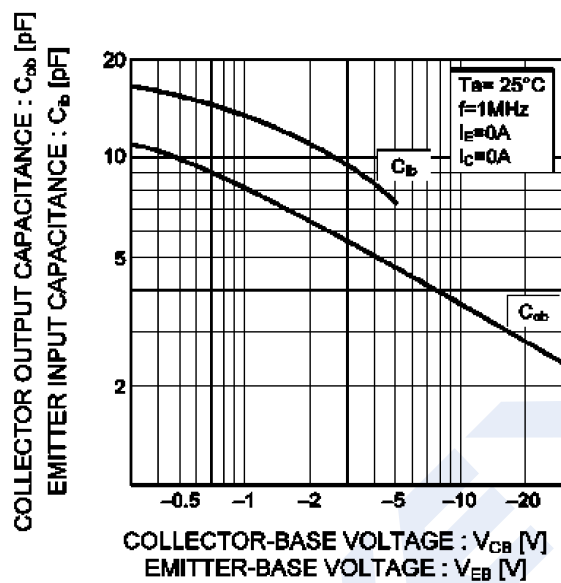


Fig.10 Safe Operating Area

